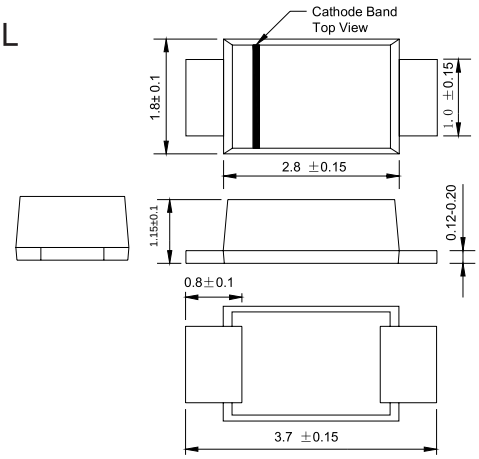
bufan GIANTION PHOTOELECTRICITY

E1A THRU E1J

■外形尺寸和印记 Outline Dimensions and Mark

SOD-123FL



Dimensions in millimeters

特征 Features

- I_o 1A
- VRRM 50V-600V
- 玻璃钝化芯片
  Glass passivated chip
- 耐正向浪涌电流能力高
  High surge current capability

用途 Applications

- 整流用 Rectifier

极限值（绝对最大额定值）
Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Conditions	E1						
				A	B	C	D	E	G	J
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	150	200	300	400	600
RMS电压最高值 Maximum RMS Voltage	V_{RMS}	V		35	70	105	140	210	280	420
正向平均电流 Average Forward Current	$I_{F(AV)}$	A	正弦半波 60Hz，电阻负载，T_L= 90 ℃ 60HZ Half-sine wave, Resistance load, T_L=120℃	1.0						
正向（不重复）浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	正弦半波60Hz，一个周期，Ta=25℃ 60Hz Half-sine wave ,1 cycle , Ta =25℃	25						
结温 Junction Temperature	T_J	℃		-55~+ 100						
储存温度 Storage Temperature	T_{STG}	℃		-55 ~ +150						

电特性（Ta=25℃ 除非另有规定）
Electrical Characteristics (T=25℃ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition		E1						
					A	B	C	D	E	G	J
正向峰值电压	V_F	V	I_F=1.0A		0.95				1.25		1.70
最大反向恢复时间 Maximum reverse recovery time	t_{rr}	ns	I_F=0.5A I_R=1A I_{RR}=0.25A		35						
反向漏电流 Peak Reverse Current	I_{RRM1}	μA	V_{RM}=V_{RRM}	Ta =25℃	5						
	I			Ta =100℃	100						
热阻(典型) Thermal Resistance(Typical)	$R_{\theta J-A}$	℃/W	结和环境之间 Between junction and ambient		85[1)]						
	$R_{\theta J-L}$		结和终端之间 Between junction and terminal		35[1)]						

■特性曲线（典型）

图1：正向电流降额曲线
FIG.1: FORWARD CURRENT DERATING CURVE

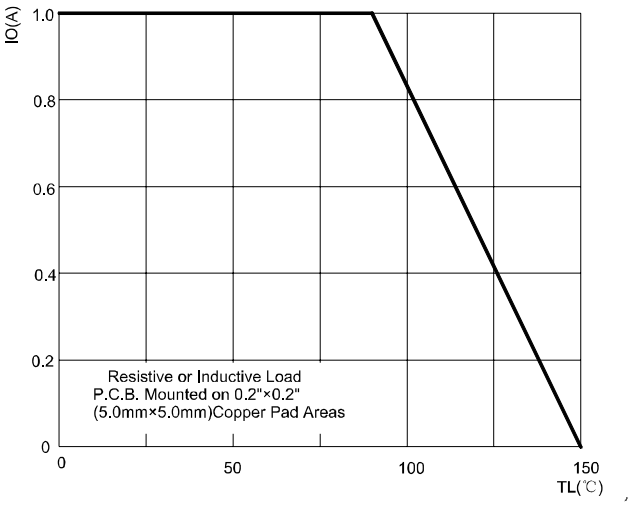


图2：最大正向浪涌冲击耐受力
FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

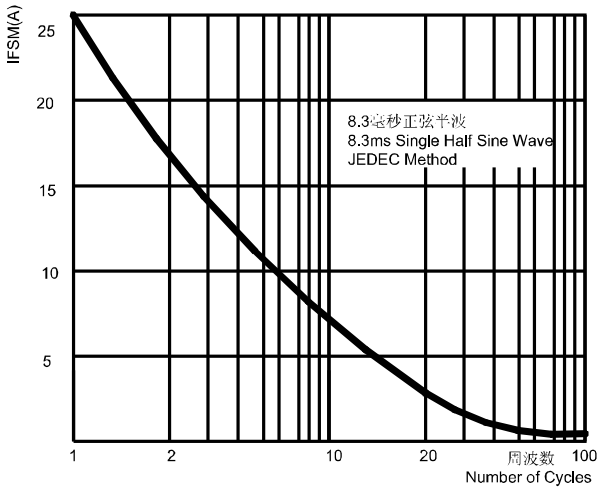


图3：典型正向特性曲线
FIG.3: TYPICAL FORWARD CHARACTERISTICS

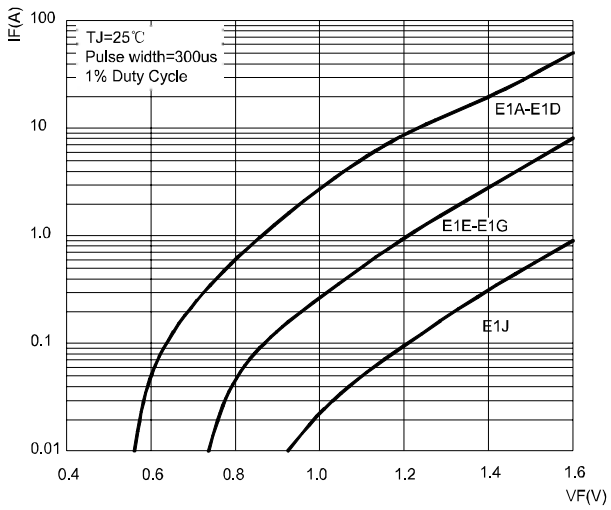


图4：典型反向特性曲线
FIG.4：TYPICAL REVERSE CHARACTERISTICS

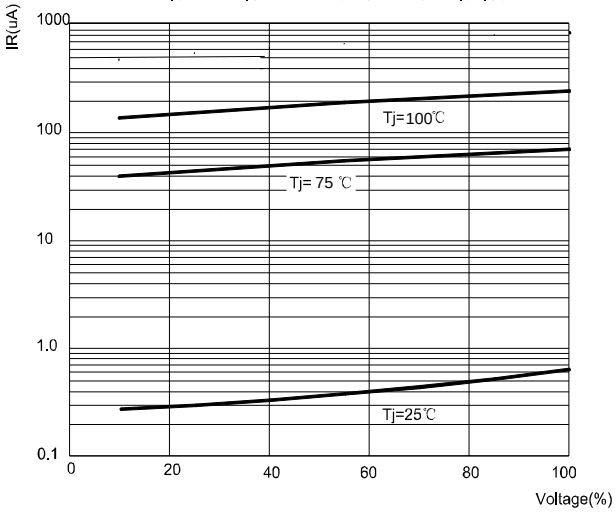


图5：反向恢复时间试验电路及测试波形示意图
FIG.5: Diagram of circuit and Testing wave form of reverse recovery time